Erratum: Energetics of Island Formation of AlAs, GaAs, and InAs on Si(100)

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The values in the last two columns of Table 1 were shifted accidentally. Below is Table 1 with corrected data. None of the analysis of the results is affected by the correction.

Table 1. The surface energies, relative to that of Si(100)2×1:As, in eV. The structures are grouped according to the number of MAs pairs added to Si(100)2×1:As and are schematically shown in Figs. 3, 4, and 5.

Structure	Theory [12] (M = Ga)	Present (M = Ga)	Present (M = Al)	Present (M = In)
Si(100)2×1:As	0.0	0.00	0.00	0.00
		1 MAs		
Si(100)-(SiAs)(MSi)As	0.48	0.44	0.63	0.62
Si(100)-(MAs)As	1.07	0.91	1.17	1.21
		2 MAs		
Si(100)-AsMAs	0.81	0.80	0.99	1.25
Si(100)-MAsSiAs	1.35	1.24	1.86	2.22
Si(100)-(SiM)As(SiM)As	1.14	1.01	1.39	1.84
Si(100)-(MSi)As(SiM)As	0.70	0.64	0.97	1.15
		3 MAs		
Si(100)-(SiAs)MAs(MSi)As	1.01	0.88	1.28	1.79
Si(100)-(SiAs)MAs(SiM)As	0.93	0.90	1.28	1.77

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